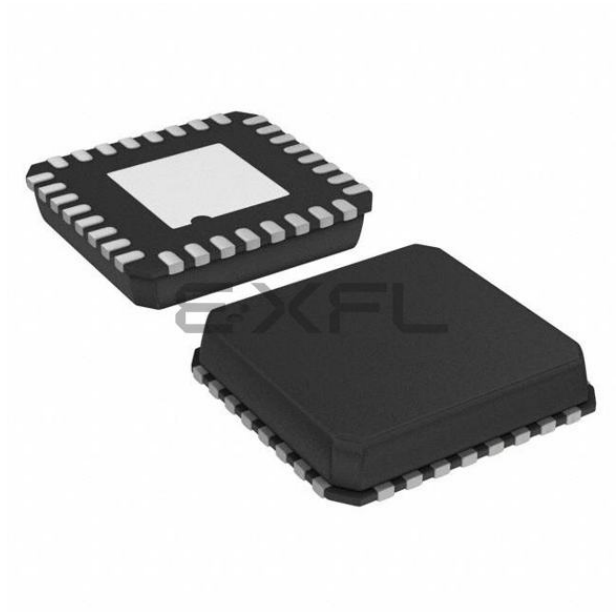


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

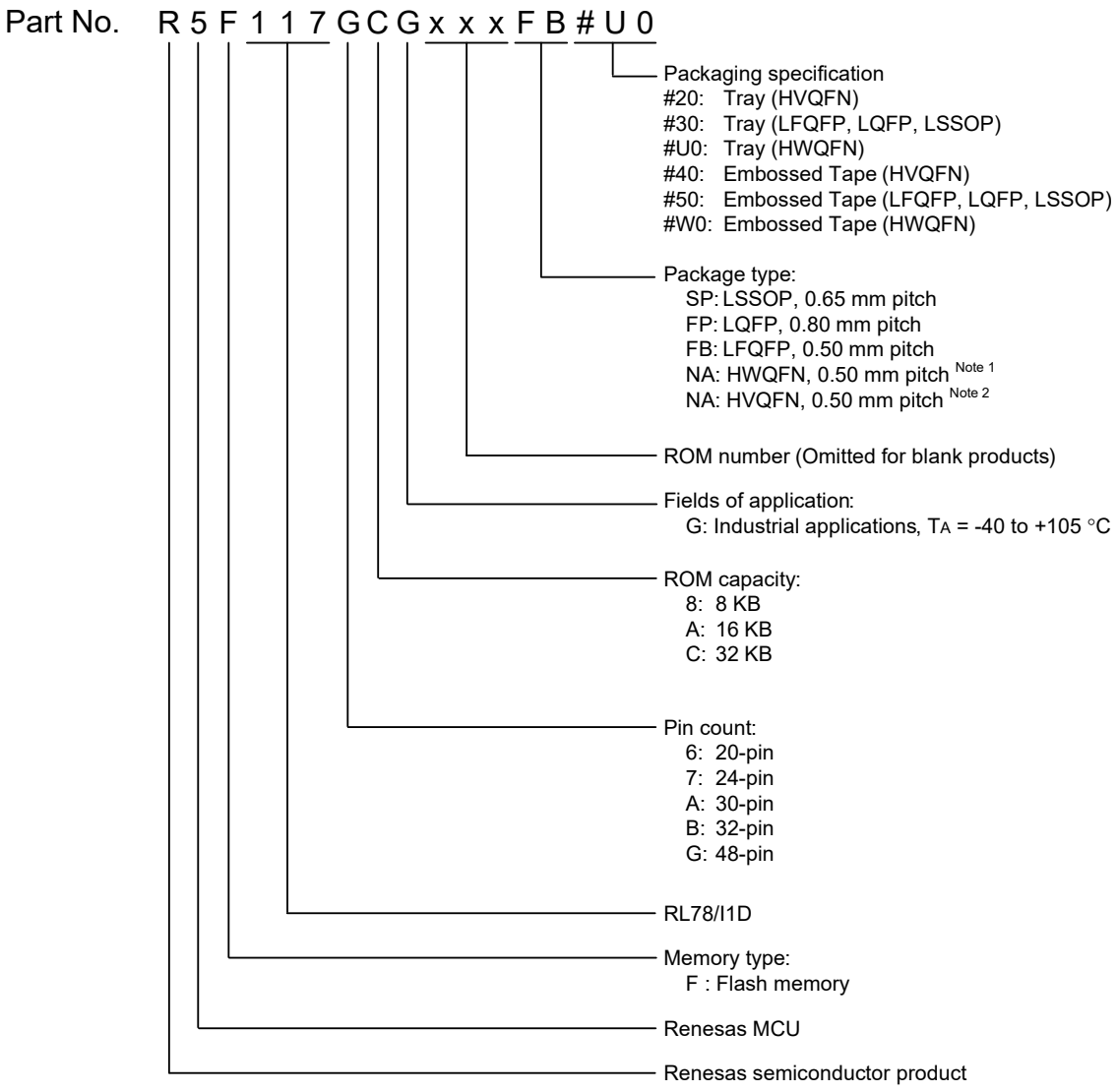
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, WDT
Number of I/O	21
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 12x8/12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f117bcgna-20

1.2 Ordering Information

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1D



Note 1. 24-pin products
Note 2. 32-pin products

1.4 Pin Identification

ANI0 to ANI13, ANI16 to ANI18 : Analog input
AV_{DD} : Analog power supply
AV_{REFM} : A/D converter reference potential (- side) input
AV_{REFP} : A/D converter reference potential (+ side) input
AV_{SS} : Analog ground
EXCLK : External clock input (main system clock)
EXCLKS : External clock input (subsystem clock)
INTP0 to INTP6 : External interrupt input
IVCMP0, IVCMP1 : Comparator input
IVREF0, IVREF1 : Comparator reference input
KR0 to KR3 : Key return
P00 to P04 : Port 0
P10 to P17 : Port 1
P20 to P25 : Port 2
P30 to P33 : Port 3
P40 : Port 4
P50 to P57 : Port 5
P60 to P63 : Port 6
P121 to P124 : Port 12
P130, P137 : Port 13
PCLBUZ0, PCLBUZ1 : Programmable clock output/buzzer output
REGC : Regulator capacitance
$\overline{\text{RESET}}$: Reset
RTC1HZ : Real-time clock correction clock (1 Hz) output
RxD0 : Receive data
SCK00, SCK01 : Serial clock input/output
SCL00, SCL01 : Serial clock input/output
SDA00, SDA01 : Serial data input/output
SI00, SI01 : Serial data input
SO00, SO01 : Serial data output
$\overline{\text{SSI00}}$: Serial interface chip select input
TI00 to TI03 : Timer input
TO00 to TO03 : Timer output
TOOL0 : Data input/output for tool
TOOLRXD, TOOLTXD : Data input/output for external device
TxD0 : Transmit data
VCOUT0, VCOUT1 : Comparator output
AMP0+, AMP1+, AMP2+, AMP3+ : Operational amplifier (+side) input
AMP0-, AMP1-, AMP2-, AMP3- : Operational amplifier (-side) input
AMP0O, AMP1O, AMP2O, AMP3O : Operational amplifier output
V_{DD} : Power supply
V_{SS} : Ground
X1, X2 : Crystal oscillator (main system clock)
XT1, XT2 : Crystal oscillator (subsystem clock)

1.6 Outline of Functions

Remark This outline describes the functions at the time when Peripheral I/O redirection register 0 (PIOR0) are set to 00H.

(1/2)

<R>

Item		20-pin	24-pin	30-pin	32-pin	48-pin
		R5F1176x (x = 8, A)	R5F1177x (x = 8, A)	R5F117Ax (x = 8, A, C)	R5F117Bx (x = A, C)	R5F117Gx (x = A, C)
Code flash memory (KB)		8 to 16 KB	8 to 16 KB	8 to 32 KB	16 to 32 KB	16 to 32 KB
Data flash memory (KB)		2 KB	2 KB	2 KB	2 KB	2 KB
RAM		0.7 to 2.0 KB	0.7 to 2.0 KB	0.7 to 3.0 KB Note	2.0 to 3.0 KB Note	2.0 to 3.0 KB Note
Address space		1 MB				
Main system clock	High-speed system clock (f_{MX})	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode:1 to 20 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode:1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode:1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode:1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode:1 MHz (V_{DD} = 1.8 to 3.6 V)				
	High-speed on-chip oscillator clock (f_{IH}) Max: 24 MHz	HS (High-speed main) mode: 1 to 24 MHz (V_{DD} = 2.7 to 3.6 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 3.6 V), LP (Low-power main) mode: 1 MHz (V_{DD} = 1.8 to 3.6 V)				
	Middle-speed on-chip oscillator clock (f_{IM}) Max: 4 MHz					
Subsystem clock	Subsystem clock oscillator (f_{SX}, f_{SXR})	—		XT1 (crystal) oscillation 32.768 kHz (TYP.): V_{DD} = 1.6 to 3.6 V		
	Low-speed on-chip oscillator clock (f_{IL})	15 kHz (TYP.): V_{DD} = 1.6 to 3.6 V				
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)				
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{IH} = 24 MHz operation)				
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)				
		—		30.5 μs (Subsystem clock oscillator clock: f_{SX} = 32.768 kHz operation)		
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.				
I/O port	Total	14	18	24	26	42
	CMOS I/O	11	15	19	21	33
	CMOS input	3	3	5	5	5
	N-ch open-drain I/O (6 V tolerance)	—	—	—	—	4
Timer	16-bit timer	4 channels				
	Watchdog timer	1 channel				
	Real-time clock	1 channel				
	12-bit interval timer	1 channel				
	8/16-bit interval timer	4 channels (8 bit) / 2 channels (16 bit)				
	Timer output	2	4	3	4	4
	RTC output	—		1 channel • 1 Hz (subsystem clock generator and RTC/other clock: f_{SX} = 32.768 kHz)		

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.

R5F117xC (x = A, B, G): Start address FF300H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(4/5)**

<R>

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2.0 mA	V_{DD} - 0.6			V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OH} = -1.5 mA	V_{DD} - 0.5			V
			1.6 V ≤ V_{DD} ≤ 3.6 V Note 1, I_{OH} = -1.0 mA	V_{DD} - 0.5			V
	V_{OH2}	P10 to P17, P20 to P25	1.6 V ≤ AV_{DD} ≤ 3.6 V Note 2, I_{OH} = -100 μA	AV_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P04, P30 to P33, P40, P50 to P57, P130	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 3.0 mA			0.6	V
			2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 1.5 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OL} = 0.6 mA			0.4	V
			1.6 V ≤ AV_{DD} ≤ 3.6 V Note 1, I_{OL} = 0.3 mA			0.4	V
	V_{OL2}	P10 to P17, P20 to P25	1.6 V ≤ AV_{DD} ≤ 3.6 V Note 2, I_{OL} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 3.0 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V Note 3, I_{OL} = 2.0 mA			0.4	V
			1.6 V ≤ AV_{DD} ≤ 3.6 V Note 1, I_{OL} = 1.0 mA			0.4	V

Note 1. Only T_A = -40 to +85°C is guaranteed.

Note 2. The condition that 2.4 V ≤ AV_{DD} ≤ 3.6 V is guaranteed when +85°C < T_A ≤ +105°C.

Note 3. The condition that 2.4 V ≤ V_{DD} ≤ 3.6 V is guaranteed when +85°C < T_A ≤ +105°C.

Caution P30 and P51 to P56 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(3/4)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode	f_{IH} = 24 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			0.37	1.83	mA
				f_{IH} = 24 MHz Note 4, T_A = +85 to +105°C	V_{DD} = 3.0 V				2.85	
				f_{IH} = 16 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			0.36	1.38	
				f_{IH} = 16 MHz Note 4, T_A = +85 to +105°C	V_{DD} = 3.0 V				2.08	
			LS (low-speed main) mode (MCSEL = 0)	f_{IH} = 8 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			250	710	µA
					V_{DD} = 2.0 V			250	710	
			LS (low-speed main) mode (MCSEL = 1)	f_{IH} = 4 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			204	400	µA
					V_{DD} = 2.0 V			204	400	
				f_{IM} = 4 MHz Note 7, T_A = -40 to +85°C	V_{DD} = 3.0 V			40	250	
					V_{DD} = 2.0 V			40	250	
<R>			LV (low-voltage main) mode	f_{IH} = 3 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			425	800	µA
					V_{DD} = 2.0 V			425	800	
			LP (low-power main) mode (MCSEL = 1)	f_{IH} = 1 MHz Note 4, T_A = -40 to +85°C	V_{DD} = 3.0 V			192	400	µA
					V_{DD} = 2.0 V			192	400	
<R>				f_{IM} = 1 MHz Note 7, T_A = -40 to +85°C	V_{DD} = 3.0 V			27	100	
					V_{DD} = 2.0 V			27	100	
			HS (high-speed main) mode	f_{MX} = 20 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		0.20	1.55	mA
						Resonator connection		0.40	1.74	
				f_{MX} = 20 MHz Note 3, T_A = +85 to +105°C	V_{DD} = 3.0 V	Square wave input			2.45	
						Resonator connection			2.57	
				f_{MX} = 10 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
				f_{MX} = 10 MHz Note 3, T_A = +85 to +105°C	V_{DD} = 3.0 V	Square wave input			1.28	
						Resonator connection			1.36	
			LS (low-speed main) mode (MCSEL = 0)	f_{MX} = 8 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		68	550	µA
						Resonator connection		120	590	
				f_{MX} = 8 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		68	550	
						Resonator connection		120	590	
			LS (low-speed main) mode (MCSEL = 1)	f_{MX} = 4 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		23	128	µA
						Resonator connection		65	200	
				f_{MX} = 1 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		23	128	
						Resonator connection		65	200	
			LP (low-power main) mode (MCSEL = 1)	f_{MX} = 4 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 3.0 V	Square wave input		10	64	µA
						Resonator connection		48	150	
				f_{MX} = 1 MHz Note 3, T_A = -40 to +85°C	V_{DD} = 2.0 V	Square wave input		10	64	
						Resonator connection		48	150	
			Subsystem clock operation	f_{SX} = 32.768 kHz, T_A = -40°C Note 5		Square wave input		0.24	0.57	µA
						Resonator connection		0.42	0.76	
				f_{SX} = 32.768 kHz, T_A = +25°C Note 5		Square wave input		0.30	0.57	
						Resonator connection		0.54	0.76	
				f_{SX} = 32.768 kHz, T_A = +50°C Note 5		Square wave input		0.35	1.17	
						Resonator connection		0.60	1.36	
				f_{SX} = 32.768 kHz, T_A = +70°C Note 5		Square wave input		0.42	1.97	
						Resonator connection		0.70	2.16	
				f_{SX} = 32.768 kHz, T_A = +85°C Note 5		Square wave input		0.80	3.37	
						Resonator connection		0.95	3.56	
				f_{SX} = 32.768 kHz, T_A = +105°C Note 5		Square wave input		1.80	17.10	
						Resonator connection		2.20	17.50	
				f_{IL} = 15 kHz, T_A = -40°C Note 6				0.40	1.22	µA
				f_{IL} = 15 kHz, T_A = +25°C Note 6				0.47	1.22	
				f_{IL} = 15 kHz, T_A = +85°C Note 6				0.80	3.30	
				f_{IL} = 15 kHz, T_A = +105°C Note 6				2.00	17.30	

(**Notes** and **Remarks** are listed on the next page.)

<R>

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The MAX values include the peripheral operating current. However, these values do not include the current flowing into the A/D converter, operational amplifier, comparator, LVD circuit, I/O ports, and on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.

Note 2. When the HALT instruction is executed in the flash memory.

Note 3. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 4. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Note 5. When the high-speed system clock, middle-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and high-speed on-chip oscillator clock are stopped. When RTCLPC = 1 and ultra-low-power consumption oscillation is set (AMPHS1, AMPHS0) = (1, 0). The values include the current flowing into the real-time clock. However, the values do not include the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, high-speed system clock, and sub clock are stopped.

Note 7. When the high-speed system clock, high-speed on-chip oscillator clock, low-speed on-chip oscillator clock, and sub clock are stopped.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{IH}: High-speed on-chip oscillator clock frequency (24 MHz max.)

Remark 3. f_{IM}: Middle-speed on-chip oscillator clock frequency (4 MHz max.)

Remark 4. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 5. f_{SX}: Sub clock frequency (XT1 clock oscillation frequency)

Remark 6. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency or low-speed on-chip oscillator clock frequency)

Remark 7. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

2.4 AC Characteristics

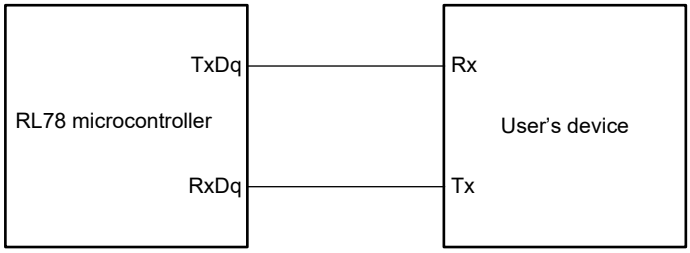
(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

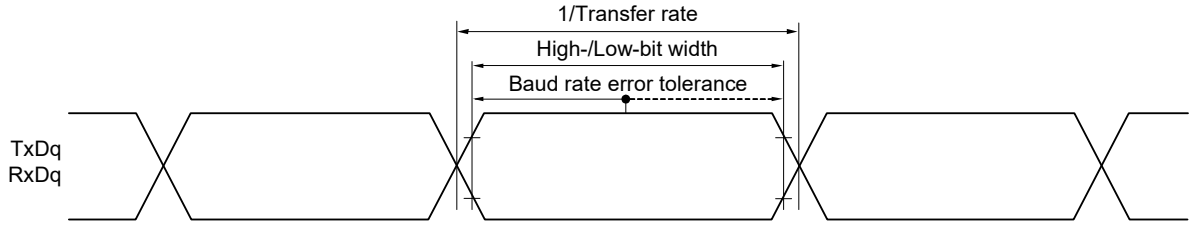
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.04167		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V PMMC. MCSEL = 0	0.125		1	µs
				1.8 V ≤ V_{DD} ≤ 3.6 V PMMC. MCSEL = 1	0.25		1	
			LP (low-power main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	1			µs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.25		1	µs
				1.6 V ≤ V_{DD} < 1.8 V	0.34		1	
		Subsystem clock (f_{SUB}) operation	f_{SX}	1.8 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	µs
			f_{IL}	1.8 V ≤ V_{DD} ≤ 3.6 V		66.7		
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.04167		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.125		1	µs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.25		1	µs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} <2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} <2.4 V			1		8	MHz
		1.6 V ≤ V_{DD} <1.8 V			1		4	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} <2.7 V			30			ns
		1.8 V ≤ V_{DD} <2.4 V			60			ns
		1.6 V ≤ V_{DD} <1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			µs
TI00 to TI03 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0), g: PIM and POM number (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = +85 to +105°C, 2.7 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V	250		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 36		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		66		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00, 01))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V	f_{MCK} > 16 MHz	8/f_{MCK}		—	—	—	—	—	—	ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		2.4 V ≤ V_{DD} ≤ 3.6 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		t_{KCY2}/2 - 66		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 30								
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		1/f_{MCK} + 40		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—								
		1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		1/f_{MCK} + 250		
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—				
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 44		2/f_{MCK} + 110		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 75							
			1.8 V ≤ V_{DD} ≤ 3.6 V		—							
			1.7 V ≤ V_{DD} ≤ 3.6 V		—		—		—		2/f_{MCK} + 220	
			1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		—			

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

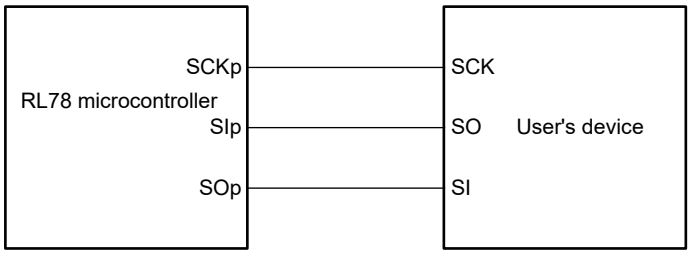
(T_A = -40 to +85°C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LP (Low-power main) mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	120		120		120		120		ns
			2.4 V ≤ V_{DD} < 2.7 V	200		200		200		200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		400		
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		1/f_{MCK} + 400		
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ V_{DD} ≤ 3.6 V	1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		ns
			2.4 V ≤ V_{DD} < 2.7 V	1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		1/f_{MCK} + 400		
		DAPmn = 1	2.7 V ≤ V_{DD} ≤ 3.6 V	120		120		120		120		ns
			2.4 V ≤ V_{DD} < 2.7 V	200		200		200		200		
			1.8 V ≤ V_{DD} < 2.4 V	—								
			1.6 V ≤ V_{DD} < 1.8 V	—		—		—		400		

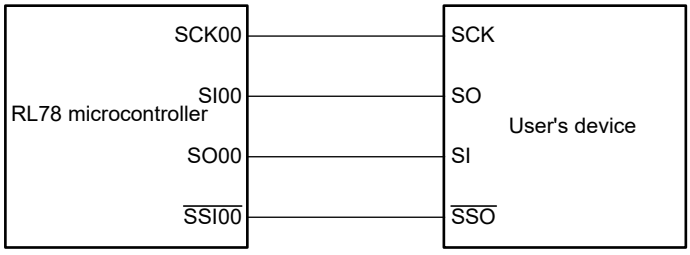
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

CSI mode connection diagram (during communication at same potential)



CSI mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00, 01)
Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 2.7 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 16		ns
		2.4 V ≤ V_{DD} < 2.7 V		t_{KCY2}/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 2.7 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 66	ns
			2.4 V ≤ V_{DD} < 2.7 V		2/f_{MCK} + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(5) During communication at same potential (simplified I²C mode)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note 1	kHz
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 220 Note 2		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(6) Communication at different potential (1.8 V, 2.5V) (UART mode) (dedicated baud rate generator output)

(T_A = +85 to +105°C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = AV_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Note 2		Transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2	Mbps
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} ≤ 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

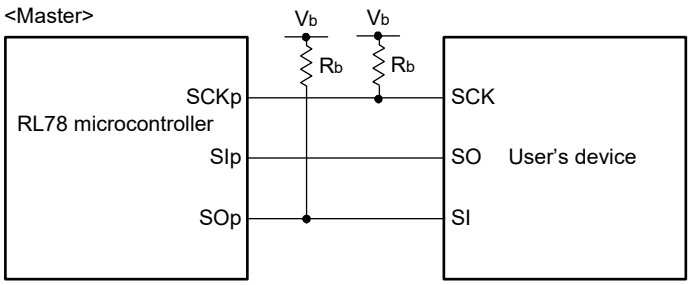
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

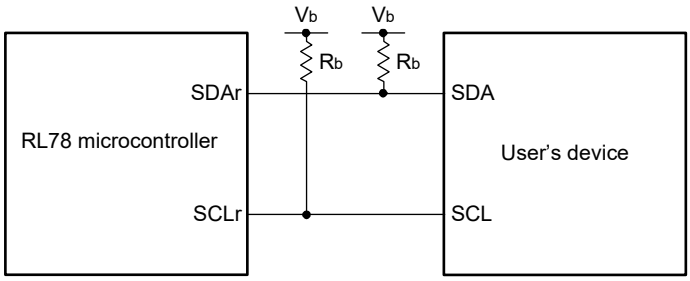


Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

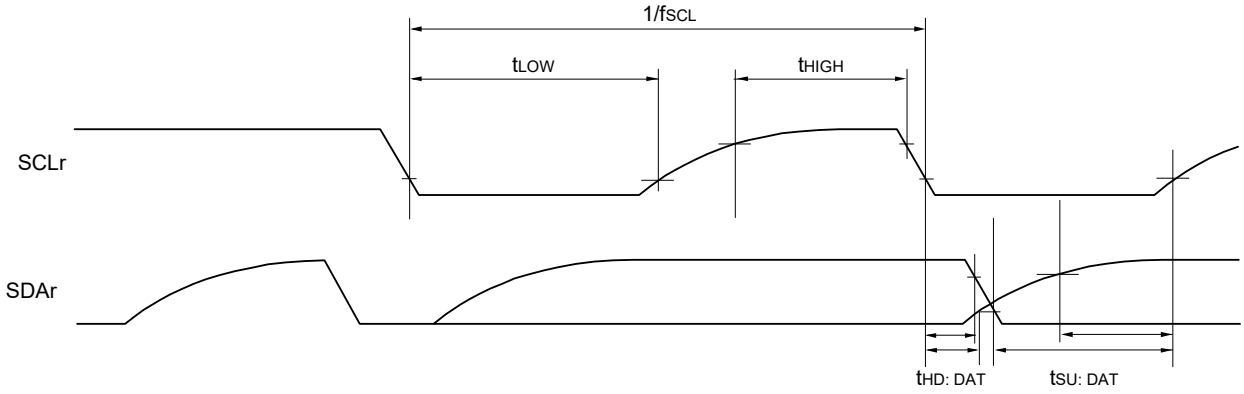
Remark 2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01), g: PIM, POM number (g = 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0, 1), mn = 00, 01)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage / Input Channel	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = AV_{DD} Reference voltage (-) = AV_{SS}	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AV_{SS}
High-accuracy channel; ANI0 to ANI13 (input buffer power supply: AV_{DD})	Refer to **2.6.1 (1)**. Refer to **2.6.1 (7)**.	Refer to **2.6.1 (2)**. Refer to **2.6.1 (7)**.	Refer to **2.6.1 (5)**. Refer to **2.6.1 (10)**.
Standard channel; ANI16 to ANI18 (input buffer power supply: V_{DD})	Refer to **2.6.1 (3)**. Refer to **2.6.1 (8)**.	Refer to **2.6.1 (4)**. Refer to **2.6.1 (9)**.	
Internal reference voltage, Temperature sensor output voltage	Refer to **2.6.1 (3)**. Refer to **2.6.1 (8)**.	Refer to **2.6.1 (4)**. Refer to **2.6.1 (9)**.	—

(7) When reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI13

(T_A = +85 to +105°C, 2.4 V ≤ AVDD = VDD ≤ 3.6 V, VSS = 0 V, AVSS = 0 V, Reference voltage (+) = AVDD, Reference voltage (-) = AVSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AVDD ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±7.5	LSB
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V	3.375			µs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±6.0	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±3.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AVDD ≤ 3.6 V			±2.0	LSB
Analog input voltage	VAIN			0		AVDD	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AVDD pin with the same potential as the VDD pin.

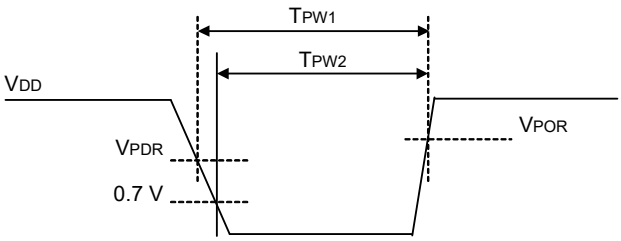
2.6.5 POR circuit characteristics

(T_A = -40 to +105°C, V_{SS} = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	T_A = -40 to +85°C	1.47	1.51	1.55	V
			T_A = +85 to +105°C	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time Note 1	T_A = -40 to +85°C	1.46	1.50	1.54	V
			T_A = +85 to +105°C	1.44	1.50	1.56	V
Minimum pulse width Note 2	T_{PW1}	Other than STOP/SUB HALT/SUB RUN	T_A = +40 to +105°C	300			µs
	T_{PW2}	STOP/SUB HALT/SUB RUN	T_A = +40 to +105°C	300			µs

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.

Note 2. Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other disputes involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawing, chart, program, algorithm, application examples.
3. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You shall not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics products.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.

   "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc.

   "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

   Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (space and undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics.
6. When using the Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat radiation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions or failure or accident arising out of the use of Renesas Electronics products beyond such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please ensure to implement safety measures to guard them against the possibility of bodily injury, injury or damage caused by fire, and social damage in the event of failure or malfunction of Renesas Electronics products, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures by your own responsibility as warranty for your products/system. Because the evaluation of microcomputer software alone is very difficult and not practical, please evaluate the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please investigate applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive carefully and sufficiently and use Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall not use Renesas Electronics products or technologies for (1) any purpose relating to the development, design, manufacture, use, stockpiling, etc., of weapons of mass destruction, such as nuclear weapons, chemical weapons, or biological weapons, or missiles (including unmanned aerial vehicles (UAVs)) for delivering such weapons, (2) any purpose relating to the development, design, manufacture, or use of conventional weapons, or (3) any other purpose of disturbing international peace and security, and you shall not sell, export, lease, transfer, or release Renesas Electronics products or technologies to any third party whether directly or indirectly with knowledge or reason to know that the third party or any other party will engage in the activities described above. When exporting, selling, transferring, etc., Renesas Electronics products or technologies, you shall comply with any applicable export control laws and regulations promulgated and administered by the governments of the countries asserting jurisdiction over the parties or transactions.
10. Please acknowledge and agree that you shall bear all the losses and damages which are incurred from the misuse or violation of the terms and conditions described in this document, including this notice, and hold Renesas Electronics harmless, if such misuse or violation results from your resale or making Renesas Electronics products available any third party.
11. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.

(Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.3.0-1 November 2016)

RENESAS

SALES OFFICES

Renesas Electronics Corporation

http://www.renesas.com

Refer to "http://www.renesas.com/" for the latest and detailed information.

Renesas Electronics America Inc.
2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

Colophon 6.0